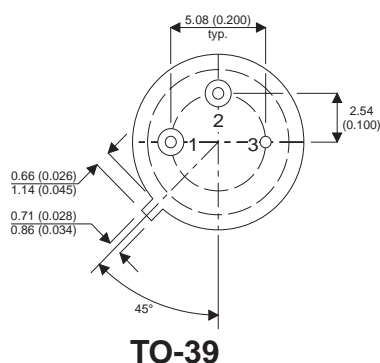
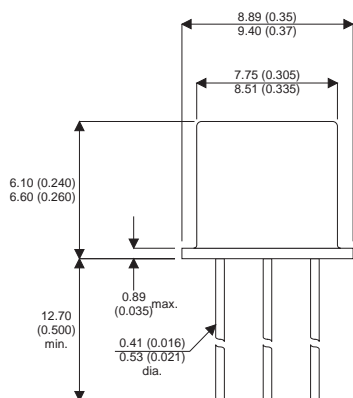


**MECHANICAL DATA**

Dimensions in mm (inches)



**TO-39**

Pin 1 – Emitter      Pin 2 – Base      Pin 3 – Collector

**ABSOLUTE MAXIMUM RATINGS**

$T_{CASE} = 25^{\circ}C$  unless otherwise stated

		2N5151	2N5153
$V_{CBO}$	Collector – Base Voltage		-100V
$V_{CEO}$	Collector – Emitter Voltage ( $I_B = 0$ )		-80V
$V_{EBO}$	Emitter – Base Voltage ( $I_C = 0$ )		-5.5V
$I_C$	Continuous Collector Current		-5A
$I_{C(PK)}$	Peak Collector Current		-10A
$I_B$	Base Current		-2.5A
$P_{tot}$	Total Dissipation at $T_{amb} = 25^{\circ}C$		1W
	$T_{case} = 50^{\circ}C$		10W
	$T_{case} = 100^{\circ}C$		6.7W
$T_{stg}$	Operating and Storage Temperature Range		-65 to +200°C
$T_j$	Junction temperature		200°C

**HIGH SPEED  
MEDIUM VOLTAGE  
SWITCHES**

**DESCRIPTION**

The 2N5151 and the 2N5153 are silicon epitaxial planar PNP transistors in jedec TO-39 metal case intended for use in switching applications.

The complementary NPN types are the 2N5152 and 2N5154 respectively

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**THERMAL DATA**

$R_{thj-case}$	Thermal Resistance Junction-case	Max	15	°C/W
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	175	°C/W

**ELECTRICAL CHARACTERISTICS FOR 2N5151** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$I_{CES}$	Collector Cut Off Current	$V_{CE} = -60V$	$V_{BE} = 0$	-1	$\mu A$	
		$V_{CE} = -100V$	$V_{BE} = 0$	-1	mA	
$I_{CEV}$	Collector Cut Off Current	$V_{CE} = -60V$	$T_{case} = 150^{\circ}C$	-500	$\mu A$	
		$V_{BE} = 2V$				
$I_{CEO}$	Collector Cut Off Current	$V_{CE} = -40V$	$I_B = 0$	-50		
$I_{EBO}$	Emitter Cut Off Current	$V_{EB} = -4V$	$I_C = 0$	-1	$\mu A$	
		$V_{EB} = -5.5V$	$I_C = 0$	-1	mA	
$V_{CEO(SUS)}$	Collector Emitter Saturation Voltage	$I_C = -100mA$	$I_B = 0$	80		
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_C = -2.5A$	$I_B = -250mA$	-0.75	V	
		$I_C = -5A$	$I_B = -500mA$	-1.5		
$V_{BE(sat)}$	Base Emitter Saturation Voltage	$I_C = -2.5A$	$I_B = -250mA$	-1.45		
		$I_C = -5A$	$I_B = -500mA$	-2.2		
$V_{BE}$	Base Emitter Voltage	$I_C = -2.5A$	$V_{CE} = -5V$	-1.45		
$h_{FE}$	DC Current Gain	$I_C = -50mA$	$V_{CE} = -5V$	20	90	
		$I_C = -2.5A$	$V_{CE} = -5V$	30		
		$I_C = -5A$	$V_{CE} = -5V$	20		
		$T_{case} = -55^{\circ}C$				
		$I_C = 2.5A$	$V_{CE} = -5V$	15		
$C_{CBO}$	Collector Base Capacitance	$I_E = 0$	$V_{CB} = -10V$		250	pF
		$f = 1MHz$				
$h_{FE}$	Small Signal Current Gain	$I_C = -0.1A$	$V_{CE} = -5V$	20		
		$I_C = -0.5A$	$V_{CE} = -5V$	3		
		$f = 20MHz$				
$t_{on}$	Turn On Time	$I_C = -5A$	$V_{CC} = 30V$	0.5	$\mu s$	
		$I_{B1} = -0.5A$				
$t_{off}$	Turn Off Time	$I_C = -5A$	$V_{CC} = 30V$	1.3	$\mu s$	
		$I_{B1} = -I_{B2} = 0.5A$				

\* Pulse test  $t_p = 300\mu s$ ,  $\delta < 2\%$

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**ELECTRICAL CHARACTERISTICS FOR 2N5153** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CES}$ Collector Cut Off Current	$V_{CE} = -60V$ $V_{BE} = 0$			-1	$\mu A$
	$V_{CE} = -100V$ $V_{BE} = 0$			-1	mA
$I_{CEV}$ Collector Cut Off Current	$V_{CE} = -60V$ $T_{case} = 150^{\circ}C$ $V_{BE} = 2V$			-500	$\mu A$
$I_{CEO}$ Collector Cut Off Current	$V_{CE} = -40V$ $I_B = 0$			-50	
$I_{EBO}$ Emitter Cut Off Current	$V_{EB} = -4V$ $I_C = 0$			-1	$\mu A$
	$V_{EB} = -5.5V$ $I_C = 0$			-1	mA
$V_{CEO(SUS)}$ Collector Emitter Saturation Voltage	$I_C = -100mA$ $I_B = 0$	80			
$V_{CE(sat)}$ Collector Emitter Saturation Voltage	$I_C = -2.5A$ $I_B = -250mA$			-0.75	V
	$I_C = -5A$ $I_B = -500mA$			-1.5	
$V_{BE(sat)}$ Base Emitter Saturation Voltage	$I_C = -2.5A$ $I_B = -250mA$			-1.45	
	$I_C = -5A$ $I_B = -500mA$			-2.2	
$V_{BE}$ Base Emitter Voltage	$I_C = -2.5A$ $V_{CE} = -5V$			-1.45	
$h_{FE}$ DC Current Gain	$I_C = -50mA$ $V_{CE} = -5V$	50			200
	$I_C = -2.5A$ $V_{CE} = -5V$	70			
	$I_C = -5A$ $V_{CE} = -5V$	40			
	$T_{case} = -55^{\circ}C$ $I_C = 2.5A$ $V_{CE} = -5V$	35			
$C_{CBO}$ Collector Base Capacitance	$I_E = 0$ $V_{CB} = -10V$ $f = 1MHz$			250	pF
$h_{FE}$ Small Signal Current Gain	$I_C = -0.1A$ $V_{CE} = -5V$ $f = 1KHz$	50			
	$I_C = -0.5A$ $V_{CE} = -5V$ $f = 20MHz$	3.5			
$t_{on}$ Turn On Time	$I_C = -5A$ $V_{CC} = 30V$ $I_{B1} = -0.5A$		0.5		$\mu s$
$t_{off}$ Turn Off Time	$I_C = -5A$ $V_{CC} = 30V$ $I_{B1} = -I_{B2} = 0.5A$		1.3		$\mu s$

\* Pulse test  $t_p = 300\mu s$ ,  $\delta < 2\%$